

N-channel 60 V, 6.0 mΩ logic level MOSFET in LFPAK56 8 May 2013 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

ck reference data							
Parameter	Conditions		Min	Тур	Max	Unit	
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V	
drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	100	А	
total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	195	W	
eristics	·						
drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	4.6	6	mΩ	
Dynamic characteristics							
gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 48 V; Fig. 13: Fig. 14		-	11.1	-	nC	
	drain-source voltage drain current total power dissipation eristics drain-source on-state resistance acteristics	ParameterConditionsdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $V_{GS} = 5 \ ^{\circ}V; T_{mb} = 25 \ ^{\circ}C; Fig. 1$ total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 2$ teristicsdrain-source on-state resistanceVGS = 5 \ V; ID = 25 \ A; Tj = 25 \ ^{\circ}C; Fig. 11	ParameterConditionsdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $V_{GS} = 5 \ ^{\circ}C; T_{mb} = 25 \ ^{\circ}C; Fig. 1$ total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 2$ teristicsdrain-source on-state resistanceV_{GS} = 5 \ ^{\circ}V; I_D = 25 \ ^{\circ}C; Fig. 11tracteristicsgate-drain charge $V_{GS} = 5 \ ^{\circ}V; I_D = 25 \ ^{\circ}V; V_{DS} = 48 \ ^{\circ}V;$	ParameterConditionsMindrain-source voltage $T_j \ge 25 ^\circ\text{C}; T_j \le 175 ^\circ\text{C}$ -drain current $V_{GS} = 5 ^\circ\text{C}; T_{mb} = 25 ^\circ\text{C}; Fig. 1$ [1]total power dissipation $T_{mb} = 25 ^\circ\text{C}; Fig. 2$ -teristicsdrain-source on-state resistance $V_{GS} = 5 ^\circ\text{V}; I_D = 25 ^\circ\text{C}; Fig. 11$ -cateristicsgate-drain charge $V_{GS} = 5 ^\circ\text{V}; I_D = 25 ^\circ\text{A}; V_{DS} = 48 ^\circ\text{V};$ -	ParameterConditionsMinTypdrain-source voltage $T_j \ge 25 \ ^{\circ}C; T_j \le 175 \ ^{\circ}C$ drain current $V_{GS} = 5 \ V; T_{mb} = 25 \ ^{\circ}C; Fig. 1$ [1]-total power dissipation $T_{mb} = 25 \ ^{\circ}C; Fig. 2$ remetric currentdrain-source on-stateV_{GS} = 5 \ V; I_D = 25 \ A; T_j = 25 \ ^{\circ}C; Fig. 11a drain-source on-statev_{GS} = 5 \ V; I_D = 25 \ A; T_j = 25 \ ^{\circ}C; Fig. 11a drain-source on-statev_{GS} = 5 \ V; I_D = 25 \ A; T_j = 25 \ ^{\circ}C; Fig. 11a drain-source on-statev_{GS} = 5 \ V; I_D = 25 \ A; T_j = 25 \ ^{\circ}C; Fig. 11a drain-source on-statev_{GS} = 5 \ V; I_D = 25 \ A; V_{DS} = 48 \ V;a drain chargeV_{GS} = 5 \ V; I_D = 25 \ A; V_{DS} = 48 \ V;	ParameterConditionsMinTypMaxdrain-source voltage $T_j \ge 25 ^\circ\text{C}; T_j \le 175 ^\circ\text{C}$ 60drain current $V_{GS} = 5 ^\circ\text{C}; T_{mb} = 25 ^\circ\text{C}; Fig. 1$ [1]100total power dissipation $T_{mb} = 25 ^\circ\text{C}; Fig. 2$ 195reristicsdrain-source on-state resistance $V_{GS} = 5 ^\circ\text{C}; Fig. 2$ -4.66racteristicsgate-drain charge $V_{GS} = 5 ^\circ\text{C}; I_D = 25 ^\circ\text{C}; Fig. 11$ -11.1-	

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	a	G-UFT4
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9Y6R0-60E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y6R0-60E	96E060

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; Pulsed$	[1][2]	-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>	[3]	-	100	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	85	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 4		-	479	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	195	W

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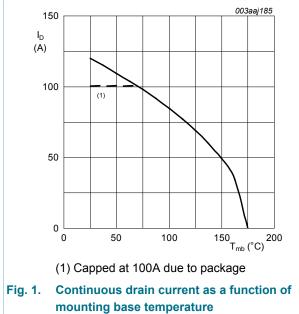
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Symbol	Parameter	Conditions		Min	Мах	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	479	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 100 \; {\sf A}; {\sf V}_{\sf sup} \le 60 \; {\sf V}; {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{\sf j(init)} = 25 \; {\rm ^{\circ}C}; \; {\sf unclamped}; \\ & {\sf Fig. \; 3} \end{split}$	[4][5]	-	127	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_{j}$ and or $\rm V_{GS}$ [1]
- [2]
- Continuous current is limited by package. [3]
- [4] [5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- Refer to application note AN10273 for further information.



 $V_{GS} \ge 5V$

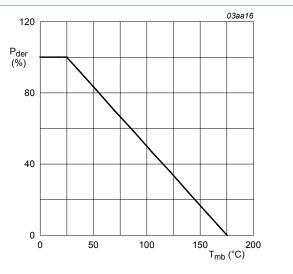
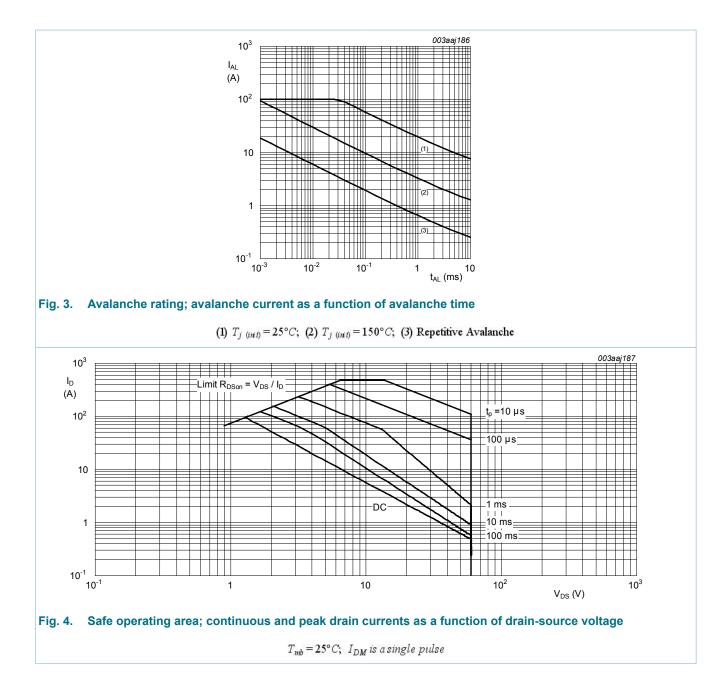


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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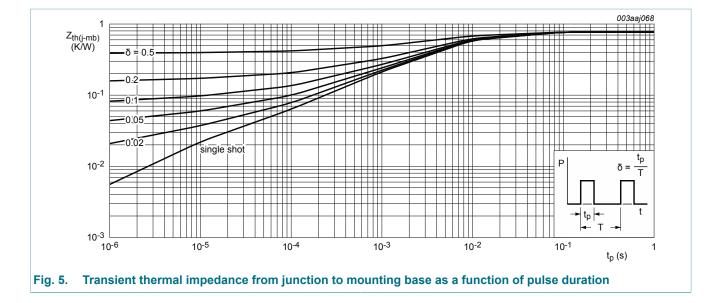
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	0.77	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.5	-	-	V
I _{DSS} d	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.07	10	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS} gate leakage current	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	-	4.6	6	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	4	5.2	mΩ
	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	13.6	mΩ	
Dynamic ch	naracteristics		1			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	39.4	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	12.3	-	nC

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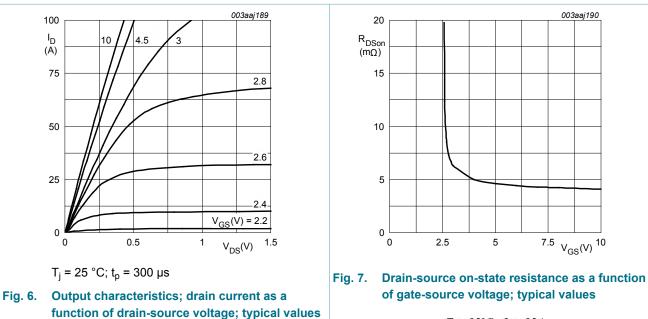
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{GD}	gate-drain charge		-	11.1	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	4739	6319	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	391	469	pF
C _{rss}	reverse transfer capacitance		-	202	277	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω	-	24	-	ns
t _r	rise time		-	44	-	ns
t _{d(off)}	turn-off delay time	-	-	60	-	ns
t _f	fall time		-	37	-	ns
Source-dra	iin diode	· · · · ·				
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	I_{S} = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	26	-	ns
Qr	recovered charge	V _{DS} = 25 V	-	23	-	nC

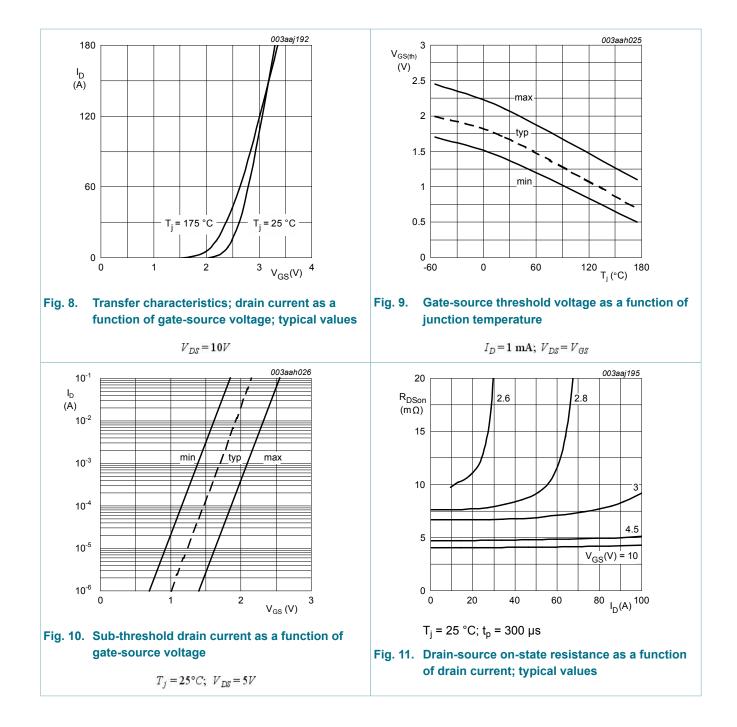


 $T_j = 25^{\circ}C; \ I_D = 25A$

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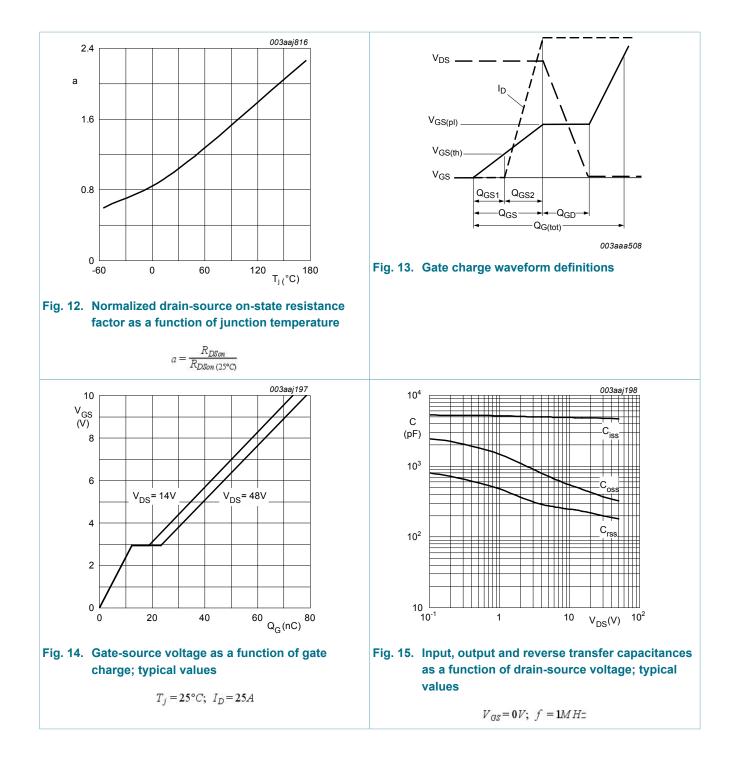
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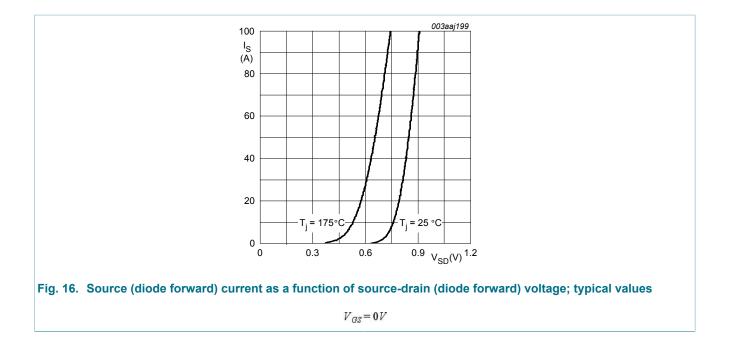
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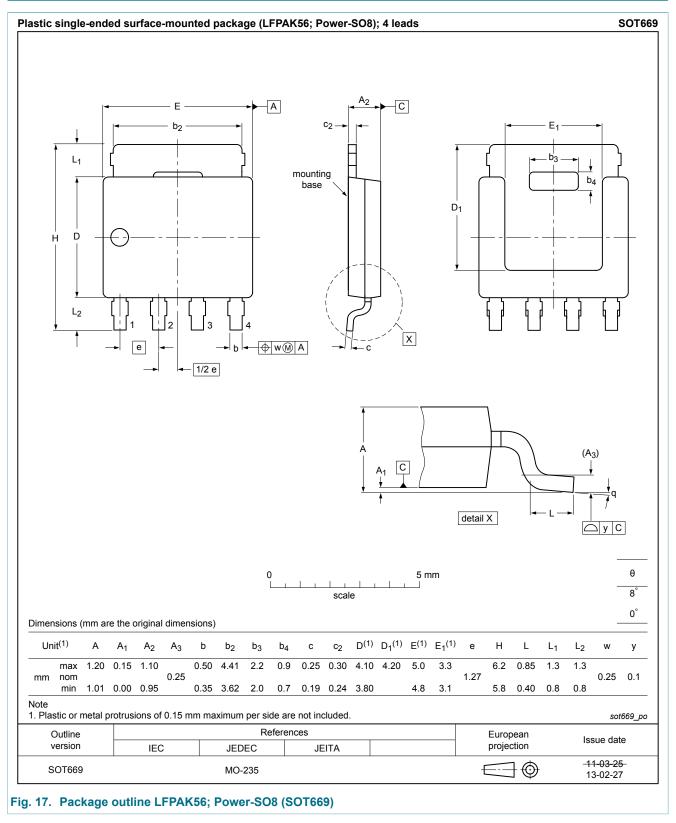
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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	Features and benefits

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